

July 26, 2004

Reference to the patent application:

Examiner: Ngan Ngo  
Art unit: 2814  
Application number: 10/797,339  
Filing date: March/10/2004  
First named inventor: Hui Peng  
Confirmation number: 4306  
Application title: Group III-V Compound Semiconductor High Brightness White of Desire Color LEDs

Dear Examiner Ngan Ngo,

Thanks for the letter of "Office Action Summary" date mailed: 07/19/2004

Per your requirement, I elect claims 1-22 to be examined, and there is no added claim. The list of all claims 1-22 is attached below, claims 1-22 are exactly the same as that originally submitted in my patent application.

If you have further instruction, please let me know. I will fax to you this letter, if you receive it, please let me know at [jimmy121790@yahoo.com](mailto:jimmy121790@yahoo.com). Thank you very much.

Really appreciate your consideration.

Best Regards

Hui Peng

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Claims:

What is claim is:

1. A high brightness light emitting diode (LED) emitting light of white or desire color, comprising:  
a substrate;  
an epitaxial layer comprising a first-type cladding layer .....
2. The high brightness light emitting diode (LED) of claim 1, further comprises a transition active layer .....
3. The high brightness light emitting diode (LED) of claim 2, wherein a material system of said transition active layer.....
4. The high brightness light emitting diode (LED) of claim 1, further comprises a buffer layer .....
5. The high brightness light emitting diode (LED) of claim 1, further comprises a current

spreading layer .....

6. The high brightness light emitting diode (LED) of claim 1, wherein a material system of said first active layer .....
7. The high brightness light emitting diode (LED) of claim 1, wherein a material system of said second active layer .....
8. The high brightness light emitting diode (LED) of claim 1, wherein a material system of said first cladding layer.....
9. The high brightness light emitting diode (LED) of claim 1, wherein a material system of said second cladding layer.....
10. A high brightness light emitting diode (LED) emitting light of white or desire color, comprising:  
a submount;  
an epitaxial layer comprising a first-type cladding layer,.....
11. The high brightness light emitting diode (LED) of claim 10, further comprises a transition active layer.....
12. The high brightness light emitting diode (LED) of claim 11, wherein a material system of said transition active layer.....
13. The high brightness light emitting diode (LED) of claim 10, further comprises a current spreading layer .....
14. The high brightness light emitting diode (LED) of claim 10, further comprises a reflector/Ohmic layer .....
15. The high brightness light emitting diode (LED) of claim 14, wherein said reflector/Ohmic layer comprises materials .....
16. The high brightness light emitting diode (LED) of claim 10, wherein a material system of said first active layer.....
17. The high brightness light emitting diode (LED) of claim 10, wherein a material system of said second active layer.....
18. The high brightness light emitting diode (LED) of claim 10, wherein a material system of said first cladding layer.....
19. The high brightness light emitting diode (LED) of claim 10, wherein a material system of said second cladding layer .....
20. The high brightness light emitting diode (LED) of claim 10, wherein said first electrode is patterned .....
21. The high brightness light emitting diode (LED) of claim 20, wherein said patterned first electrode is.....
22. The high brightness light emitting diode (LED) of claim 20, wherein said patterned first electrode is .....